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ZHCS100-NOVEMBER 2011

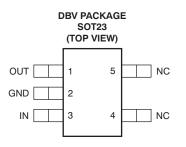
# 24-V 输入电压, 150-mA, 超低 IQ 低压差稳压器

### 特性

- 宽输入电压范围: 2.5 V 至24 V
- 低 3.2-µA静态电流
- 接地引脚电流: 在 lout 为100-mA时为3.4 µA
- 与任何电容器 (> 0.47 µF)
- 采用 SOT23-5 封装
- 工作结点温度范围:
  -40°C 至 +125°C

### 应用

- 超低功耗微处理器
- 电子仪表
- 火警/烟感系统
- 手持式外设
- 工业汽车应用
- 远程控制器
- Zigbee™ 网络
- PDA
- 便携式、电池供电型仪器

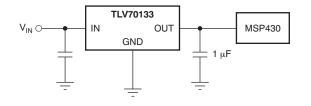


### 说明

TLV701xx 系列低压差 (LDO) 稳压器是超低静态电流 设备,设计用于极度电源敏感的应用。在完全负载电 流和周围环境温度范围内,静态电流保持恒定。这些 设备都是低功率微控制器理想的电源管理附件,例如 MSP430.

TLV701xx 运行在 2.5 V 至 24 V输入电压范围内。因此,对于电池供电系统和产生大量线路瞬变的工业应用来说,此款设备都是不错的选择。

TLV701xx 采用 3-mm × 3-mm SOT23-5 封装,此种 封装非常适合高成本有效性的主板制造。



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TLV701xx

## TLV701xx



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This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### AVAILABLE OPTIONS<sup>(1)</sup>

PRODUCT V <sub>OUT</sub>								
	XX is nominal output voltage (for example, 30 = 3.0 V) YYY is Package Designator Z is Package Quantity							

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or visit the device product folder at www.ti.com.

### ABSOLUTE MAXIMUM RATINGS<sup>(1)</sup>

Over operating free-air temperature range, unless otherwise noted.

		VALUE	UNIT	
		MIN	MAX	
Voltage <sup>(2)</sup>	IN	-0.3	24	V
Current source	OUT	Internally limite		
Temperature	Operating junction, T <sub>J</sub>	-40	+150	°C
	Storage, T <sub>stg</sub>	-65	+150	°C
Electrostatic Discharge Rating <sup>(3)</sup>	Human body model (HBM) QSS 009-105 (JESD22-A114A)		2	kV
	Charged device model (CDM) QSS 009-147 (JESD22-C101B.01)		500	V

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods my affect device reliability.

(2) All voltages are with respect to network ground terminal.

(3) ESD testing is performed according to the respective JESD22 JEDEC standard.

### THERMAL INFORMATION

		TLV701XX	
	THERMAL METRIC <sup>(1)</sup>	DBV	UNITS
		5 PINS	
$\theta_{JA}$	Junction-to-ambient thermal resistance	213.1	
θ <sub>JCtop</sub>	Junction-to-case (top) thermal resistance	110.9	
$\theta_{JB}$	Junction-to-board thermal resistance	97.4	°0 111
Ψ <sub>JT</sub>	Junction-to-top characterization parameter	22.0	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	78.4	
θ <sub>JCbot</sub>	Junction-to-case (bottom) thermal resistance	n/a	

(1) 有关传统和新的热度量的更多信息,请参阅 /C 封装热度量 应用报告 SPRA953。



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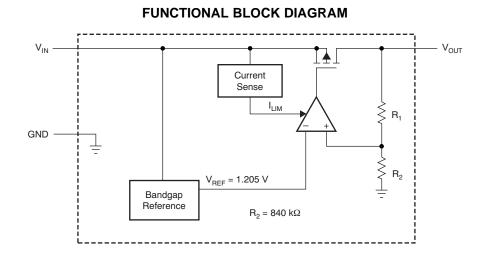
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# ELECTRICAL CHARACTERISTICS: $T_A = +25^{\circ}C$

All values are at  $T_A = +25^{\circ}C$ ,  $V_{IN} = V_{OUT(nom)} + 1 V$ ,  $I_{OUT} = 1 mA$ , and  $C_{OUT} = 1 \mu F$ , unless otherwise noted.

			ТІ				
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
	Input voltage range				24	V	
Vo	Output voltage range		1.2		5	V	
V <sub>OUT</sub>	DC output accuracy		-2		2	%	
$\Delta V_O$ for $\Delta V_{IN}$	Line regulation	V <sub>OUT(NOM)</sub> + 1 V < V <sub>IN</sub> < 24 V		20	50	mV	
$\Delta V_O$ for $\Delta I_{OUT}$		1 mA < I <sub>OUT</sub> < 10 mA		6		mV	
	Load regulation	1 mA < I <sub>OUT</sub> < 50 mA		19		mV	
		1 mA < I <sub>OUT</sub> < 100 mA		29	50	mV	
V <sub>DO</sub>	Decement and the res (1)	I <sub>OUT</sub> = 10 mA		75		mV	
	Dropout voltage <sup>(1)</sup>	I <sub>OUT</sub> = 50 mA		400		mV	
I <sub>CL</sub>	Output current limit	V <sub>OUT</sub> = 0 V	160		1000	mA	
I <sub>GND</sub>	Cround nin ourrent	I <sub>OUT</sub> = 0 mA		3.2	4.5	μA	
	Ground pin current	I <sub>OUT</sub> = 100 mA		3.4	5.5	μA	
PSRR	Power-supply rejection ratio	f = 100 kHz, C <sub>OUT</sub> = 10 μF		60		dB	

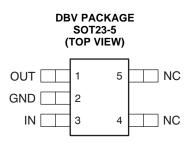
(1)  $V_{IN} = V_{OUT(NOM)} - 0.1 \text{ V}.$ 



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### **PIN CONFIGURATIONS**



### **Table 1. Pin Descriptions**

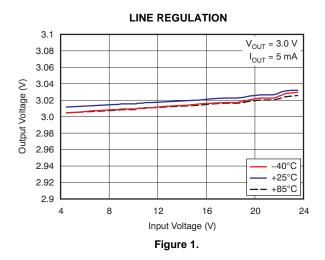
TLV701xx		
NAME	DBV	DESCRIPTION
GND	2	Ground
IN	3	Unregulated input voltage.
OUT	1	Regulated output voltage. Any capacitor 1 $\mu$ F or greater between this pin and ground is needed for stability.
NC	4, 5	No connection. This pin can be left open or tied to ground for improved thermal performance.

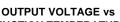


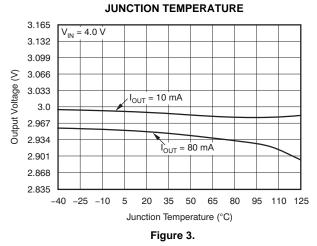
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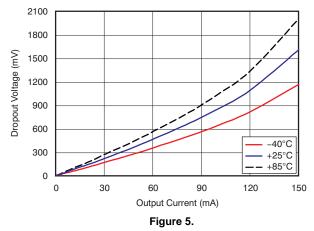
Output Voltage (V)

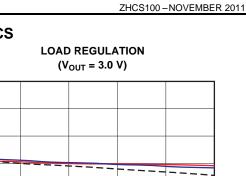






**DROPOUT VOLTAGE vs OUTPUT CURRENT** 





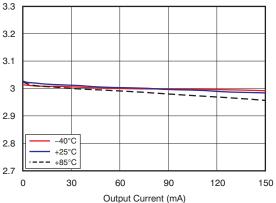
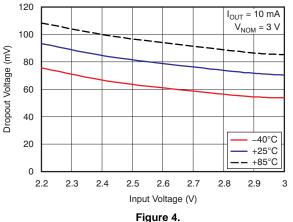
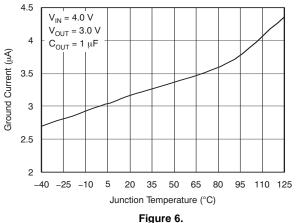


Figure 2.

**DROPOUT VOLTAGE vs INPUT VOLTAGE** 



**GROUND CURRENT vs JUNCTION TEMPERATURE** 



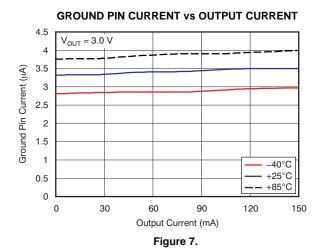
TLV701xx

TEXAS INSTRUMENTS

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**TYPICAL CHARACTERISTICS (continued)** 



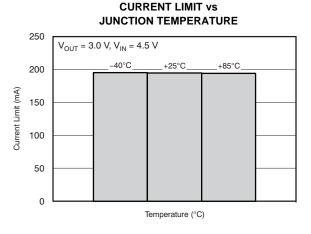
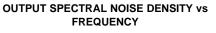
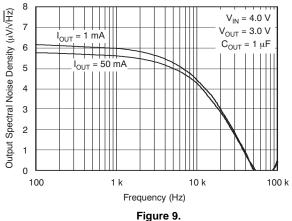
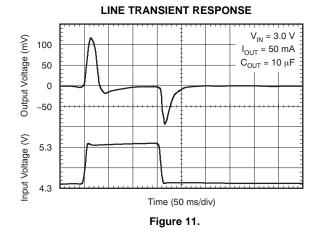


Figure 8.

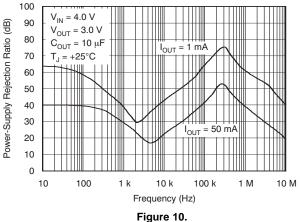




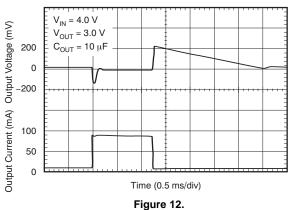




PSRR vs FREQUENCY







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TLV701xx

#### **APPLICATION INFORMATION**

The TLV701xx series of devices belong to a family of ultralow,  $I_Q$ , low-dropout (LDO) regulators.  $I_Q$  remains fairly constant over the complete output load current and temperature range. The devices are ensured to operate over a temperature range of  $-40^{\circ}$ C to  $+125^{\circ}$ C.

### INPUT AND OUTPUT CAPACITOR REQUIREMENTS

The TLV701 requires a 1-µF or larger capacitor connected between OUT and GND for stability. Ceramic or tantalum capacitors can be used. Larger value capacitors result in better transient and noise performance.

Although an input capacitor is not required for stability, when a  $0.1-\mu F$  or larger capacitor is placed between IN and GND, it counteracts reactive input sources and improves transient and noise performance. Higher value capacitors are necessary if large, fast rise time load transients are anticipated.

#### **BOARD LAYOUT RECOMMENDATIONS**

Input and output capacitors should be placed as close to the device pins as possible. To avoid interference of noise and ripple on the board, it is recommended that the board be designed with separate ground planes for  $V_{IN}$  and  $V_{OUT}$ , with the ground plane connected only at the device GND pin. In addition, the ground connection for the output capacitor should be connected directly to the device GND pin.

#### POWER DISSIPATION AND JUNCTION TEMPERATURE

To ensure reliable operation, worst-case junction temperature should not exceed +125°C. This restriction limits the power dissipation the regulator can handle in any given application. To ensure the junction temperature is within acceptable limits, calculate the maximum allowable dissipation,  $P_{D(max)}$ , and the actual dissipation,  $P_D$ , which must be less than or equal to  $P_{D(max)}$ .

The maximum power dissipation limit is determined using Equation 1:

$$\mathsf{P}_{\mathsf{D}(\mathsf{max})} = \frac{\mathsf{T}_{\mathsf{J}}\mathsf{max} - \mathsf{T}_{\mathsf{A}}}{\mathsf{R}_{\mathsf{\theta}\mathsf{J}\mathsf{A}}}$$

where:

T<sub>J</sub>max is the maximum allowable junction temperature.

 $R_{\theta,JA}$  is the thermal resistance junction-to-ambient for the package.

T<sub>A</sub> is the ambient temperature.

The regulator dissipation is calculated using Equation 2:

$$\mathsf{P}_{\mathsf{D}} = \left(\mathsf{V}_{\mathsf{IN}} - \mathsf{V}_{\mathsf{OUT}}\right) \times \mathsf{I}_{\mathsf{OUT}}$$

Power dissipation that results from quiescent current is negligible.

### **REGULATOR PROTECTION**

The TLV701xx series of LDO regulators use a PMOS-pass transistor that has a built-in back diode that conducts reverse current when the input voltage drops below the output voltage (for example, during power-down). Current is conducted from the output to the input and is not internally limited. If extended reverse voltage operation is anticipated, external limiting might be appropriate.

The TLV701xx features internal current limiting. During normal operation, the TLV701xx limits output current to approximately 250 mA. When current limiting engages, the output voltage scales back linearly until the overcurrent condition ends. Take care not to exceed the rated maximum operating junction temperature of +125°C. Continuously running the device under conditions where the junction temperature exceeds +125°C degrades device reliability.

The ability to remove heat from the die is different for each package type, presenting different considerations in the printed circuit board (PCB) layout. The PCB area around the device that is free of other components moves the heat from the device to the ambient air. Using heavier copper increases the effectiveness in removing heat from the device. The addition of plated through-holes to heat-dissipating layers also improves heatsink effectiveness. Power dissipation depends on input voltage and load conditions. Power dissipation (P<sub>D</sub>) is equal to the product of the output current and the voltage drop across the output pass element, as shown in Equation 2.

(1)

(2)



### **PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TLV70130DBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	YBVA	Samples
TLV70130DBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	YBVA	Samples
TLV70133DBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	YBWA	Samples
TLV70133DBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	YBWA	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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# **DBV0005A**



## **PACKAGE OUTLINE**

## SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. Refernce JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.

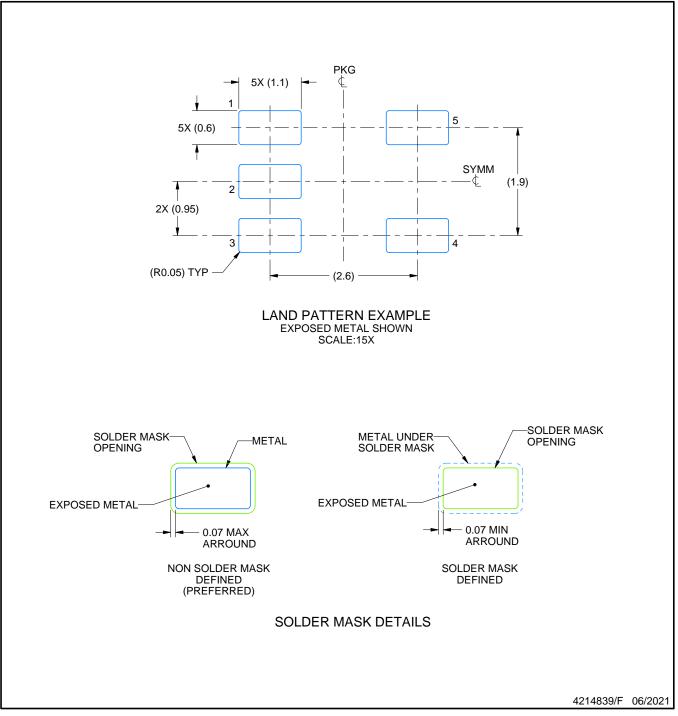


# DBV0005A

# **EXAMPLE BOARD LAYOUT**

## SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

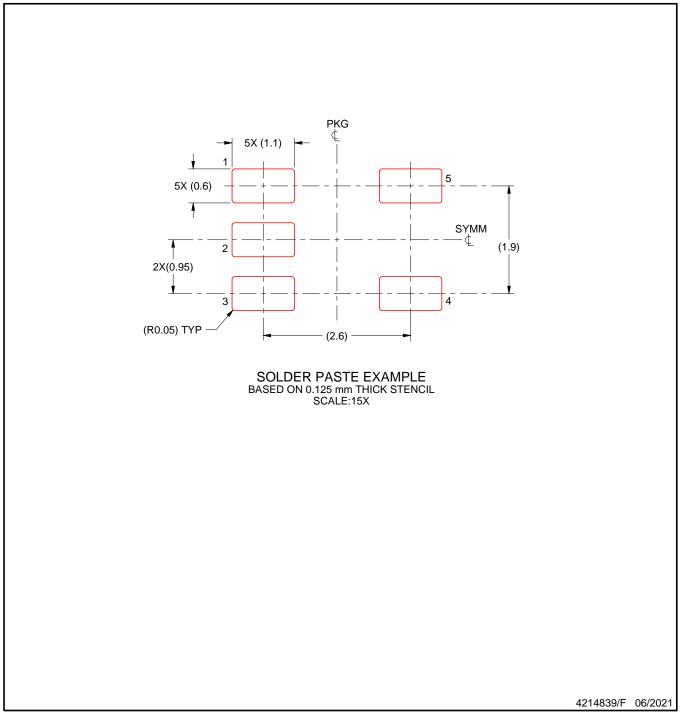


## DBV0005A

# **EXAMPLE STENCIL DESIGN**

## SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

8. Board assembly site may have different recommendations for stencil design.



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